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TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

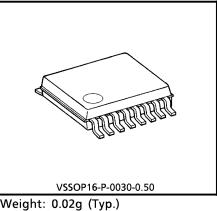
ТС7МН157FК

Quad 2 - Channel Multiplexer

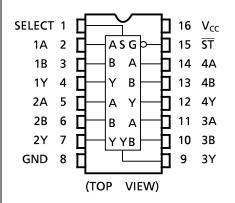
The TC7MH157 is an advanced high speed CMOS QUAD 2 - CHANNEL MULTIPLEXER fabricated with silicon gate	
C ² MOS technology. It achieves the high speed operation similar to equivalent	
Bipolar Schottky TTL while maintaining the CMOS low power	
dissipation. It consists of four 2 - input digital multiplexers with common	
select and strobe inputs.	
When the STROBE input is held "H" level, selection of data is inhibited and all the outputs become "L" level.	
The SELECT decoding determines whether the A or B inputs	
get routed to their corresponding Y outputs. An Input protection circuit ensures that 0 to 7V can be	Wei
applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and on	Pin
two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.	SE
Features:	
• High Speedt _{pd} = 4.1 ns (typ.) at V_{CC} = 5	
V	
• Low Power Dissipation $\dots I_{CC} = 4\mu A(max)$ at Ta = 25°C	
• High Noise Immunity $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$ (min)	
 Power Down Protection is provided on all inputs. Balanced Propagation Delayst_{pLH}~t_{pHL} 	
• Wide Operating Voltage Range V_{CC} (opr) = 2V~5.5V	
• Low Noise \cdots $V_{OLP} = 0.8V$ (max)	·
Truth Table	IEC

Truth Table

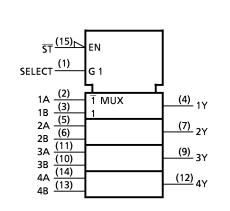
	INPUTS								
ST	SELECT	А	В	OUTPUT					
н	X	х	X	L					
L	L	L	X	L					
L	L	Н	X	н					
L	н	х	L	L					
L	н	х	н	н					
X: I	Don't Ca	re							



Pin Assignment

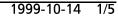


C Logic Symbol



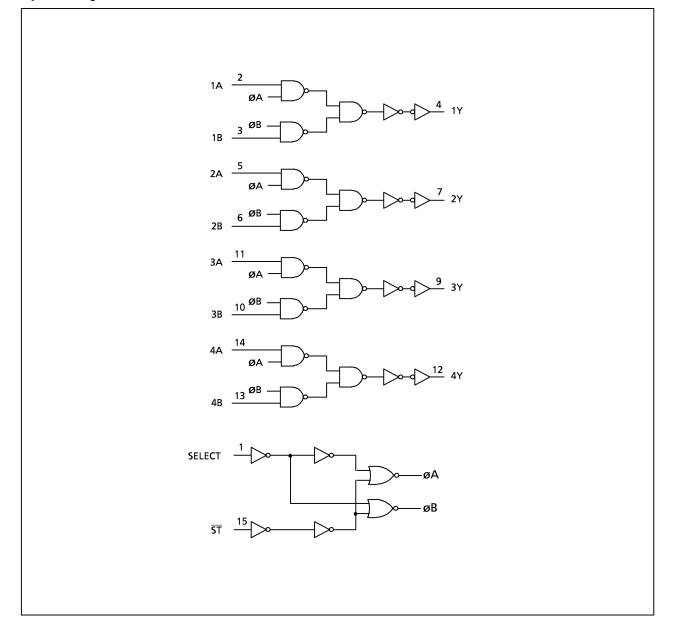
980910EBA2

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System Diagram



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Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	V
DC Output Voltage	V _{o∪T}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	Ι _{ικ}	- 20	mA
Output Diode Current	I _{ок}	±20	mA
DC Output Current	I _{OUT}	±25	mA
DC V _{CC} /Ground Current	I _{cc}	± 50	mA
Power Dissipation	PD	180	mW
Storage Temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{cc}	2.0~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	V _{OUT}	0~V _{cc}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	dt/dv	0~100 (V _{CC} = 3.3 ± 0.3V) 0~20 (V _{CC} = 5±0.5V)	ns / V

DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CO		V _{cc}	Т	a = 25°	С	Ta = — 4	40∼85°C	UNIT
FARAIVIETER		TEST CONDITION		(V)	Min	Тур.	Max	Min	Max	
High - Level				2.0	1.50	_	-	1.50	—	
Input Voltage	VIH			3.0~ 5.5	V _{cc} × 0.7		-	V _{cc} × 0.7	—	V
Low - Level				2.0	_		0.50	—	0.50	
Input Voltage	VIL			3.0~ 5.5	-		$V_{cc} \times 0.3$	_	$V_{cc} \times 0.3$	V
		., <i>,</i>		2.0	1.9	2.0	-	1.9	—	
High - Level Output Voltage	V _{OH}	V_{IH} or V_{IL}	Ι _{ΟΗ} = 50μΑ	3.0 4.5	2.9 4.4	3.0 4.5	_	2.9 4.4	_	V
			$I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		
Low - Level Output Voltage	V _{OL}	V _{1 N} =	I _{OL} = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	v
- a par i comge		$I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36	-	0.44 0.44		
Input Leakage Current	I _{IN}	$V_{IN} = 5.5V \text{ or } GND$		0~5.5	_		±0.1	_	± 1.0	
Quiescent Supply Current	I _{cc}	$V_{IN} = V_{CC} \text{ or } GND$		5.5	_	_	4.0	-	40.0	μA

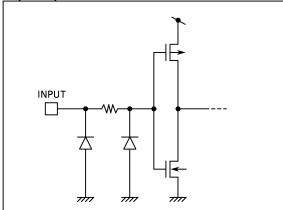
PARAMETER		TEST	TEST CONDITION		Ta = 25°C			Ta = − 40~85°C			
	SYMBOL		V _{cc} (V)	CL (pF)	Min	Тур.	Max	Min	Max		
	t _{pLH}			3.3±0.3	15	—	6.2	9.7	1.0	11.5	
Propagation Delay Time			5.5 ± 0.5	50		8.7	13.2	1.0	15.0		
(A, B-Y)	t _{pHL}		5.0 ± 0.5	15		4.1	6.4	1.0	7.5		
			5.0 ± 0.5	50	-	5.6	8.4	1.0	9.5		
Propagation Delay Time (SELECT - Y)	t _{pLH} t _{pHL}		3.3±0.3	15	_	8.4	13.2	1.0	15.5	ns	
				50		10.9	16.7	1.0	19.0		
		5	5.0 ± 0.5	15	_	5.3	8.1	1.0	9.5		
			5.0 ± 0.5	50	_	6.8	10.1	1.0	11.5		
		t _{oLH} 3.3 ± 0.	22+02	15	_	8.7	13.6	1.0	16.0		
Propagation Delay Time	t _{pLH}		5.5 ± 0.5	50	_	11.2	17.1	1.0	19.5		
(ST -Y)	t _{pLH} t _{pHL}		5.0 ± 0.5	15	-	5.6	8.6	1.0	10.0		
		5.0 ± 0.5	50	—	7.1	10.6	1.0	12.0			
Input Capacitance	C _{IN}				_	4	10	-	10		
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	20	—	-	—	pF	

AC Electrical Characteristics (Input $t_r = t_f = 3ns$)

(Note 1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC (opr.)} = C_{PD} · V_{CC} · f_{IN} + I_{CC} / 4 (per bit) Noise Characteristics (Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDIT	Ta =			
PARAIVIETER	STIVIBOL		V _{cc} (V)	Тур.	Limit	
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	$C_L = 50 pF$	5.0	0.3	0.8	<
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	$C_L = 50 pF$	5.0	- 0.3	- 0.8	<
Minimum High Level Dynamic Input Voltage	V _{IHD}	$C_L = 50 pF$	5.0	_	3.5	<
Maximum Low Level Dynamic Input Voltage	V _{ILD}	$C_L = 50 pF$	5.0	_	1.5	V

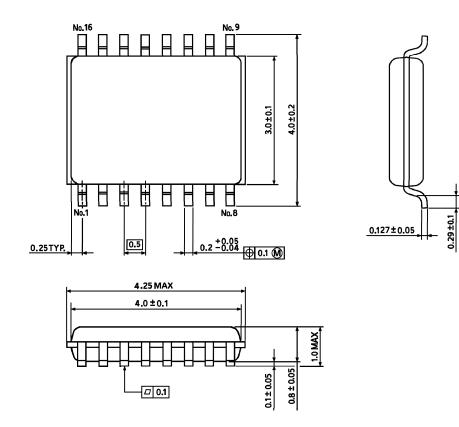
Input Equivalent Circuit



Outline Drawing

VSSOP16-P-0030-0.50

Unit: mm



Weight: 0.02g (Typ.)